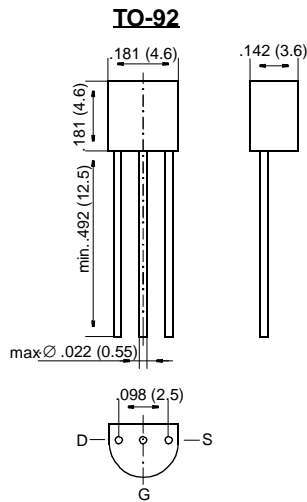


BS223

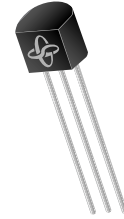
DMOS Transistors (P-Channel)



Dimensions in inches and (millimeters)

FEATURES

- ◆ High input impedance
- ◆ Low gate threshold voltage
- ◆ Low drain-source ON resistance
- ◆ High-speed switching
- ◆ No minority carrier storage time
- ◆ CMOS logic compatible input
- ◆ No thermal runaway
- ◆ No secondary breakdown



MECHANICAL DATA

Case: TO-92 Plastic Package

Weight: approx. 0.18 g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit
Drain-Source Voltage	$-V_{DSS}$	60	V
Drain-Gate Voltage	$-V_{DGS}$	60	V
Gate-Source Voltage (pulsed)	V_{GS}	± 20	V
Drain Current (continuous) at $T_{amb} = 25\text{ }^{\circ}\text{C}$	$-I_D$	1	A
Power Dissipation at $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	830 ¹⁾	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_S	-65 to +150	$^{\circ}\text{C}$

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.

Inverse Diode

	Symbol	Value	Unit
Max. Forward Current (continuous) at $T_{amb} = 25\text{ }^{\circ}\text{C}$	I_F	1	A
Forward Voltage Drop (typ.) at $V_{GS} = 0\text{ V}$, $I_F = 1\text{ mA}$, $T_j = 25\text{ }^{\circ}\text{C}$	V_F	1.0	V

BS223

ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage at $-I_D = 100 \mu\text{A}$, $V_{GS} = 0 \text{ V}$	$-V_{(BR)DSS}$	60	70	–	V
Gate-Body Leakage Current, Forward at $-V_{GSF} = 20 \text{ V}$, $V_{DS} = 0 \text{ V}$	$-I_{GSSF}$	–	–	500	nA
Gate-Body Leakage Current, Reverse at $-V_{GSR} = 20 \text{ V}$, $V_{DS} = 0 \text{ V}$	$-I_{GSSR}$	–	–	500	nA
Drain Cutoff Current at $-V_{DS} = 60 \text{ V}$, $V_{GS} = 0 \text{ V}$	$-I_{DSS}$	–	–	250	μA
Gate-Source Threshold Voltage at $V_{GS} = V_{DS}$, $-I_D = 250 \mu\text{A}$	$-V_{GS(th)}$	1	1.5	3	V
Drain-Source ON Resistance at $-V_{GS} = 10 \text{ V}$, $-I_D = 600 \text{ mA}$	$R_{DS(on)}$	–	0.7	0.8	Ω
Capacitance at $-V_{DS} = 25 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$ Input Capacitance Output Capacitance Feedback Capacitance	C_{iSS} C_{oSS} C_{rSS}	– – –	350 150 35	– – –	pF pF pF
Switching Times at $-V_{GS} = 10 \text{ V}$, $-V_{DS} = 10 \text{ V}$, $R_D = 100 \Omega$ Turn-On Time Turn-Off Time	t_{on} t_{off}	– –	40 100	– –	ns ns
Thermal Resistance Junction to Ambient Air	R_{thJA}	–	–	150 ¹⁾	K/W

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.